



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



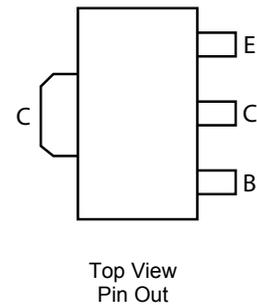
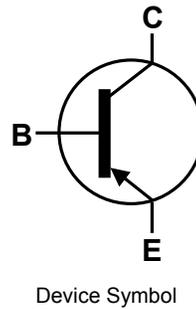
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## Features

- $BV_{CEO} > -25V$
- $I_C = -3A$  high Continuous Current
- $I_{CM} = -8A$  Peak Pulse Current
- Low saturation voltage  $V_{CE(sat)} < -320mV @ -3A$
- $h_{FE}$  specified up to -8A for high current gain hold up
- Complementary NPN Type: NK-FCX688B

## Mechanical Data

- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.05 grams (Approximate)



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-3	A
Peak Pulse Current	I <sub>CM</sub>	-8	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

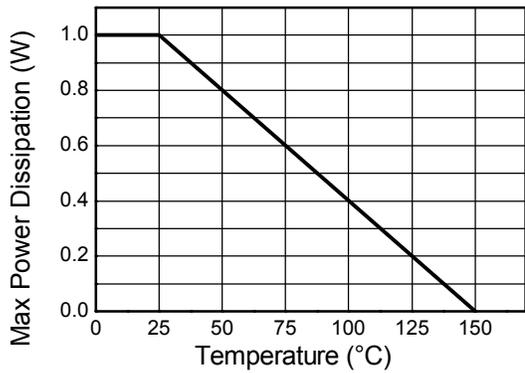
Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 5) 1	W
		(Note 6) 2	
Thermal Resistance, Junction to Ambient Air	R <sub>θJA</sub>	(Note 5) 125	°C/W
		(Note 6) 62.5	
Thermal Resistance, Junction to Leads	R <sub>θJL</sub>	5.31	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 8)

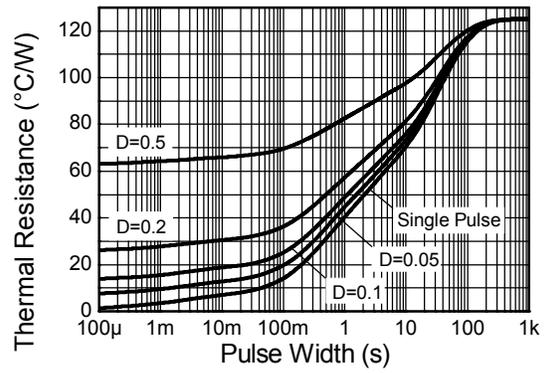
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.
  6. Same as note (5), except the device is mounted on 40mm X 40mm FR4 PCB.
  7. Thermal resistance from junction to solder-point (at the end of collector lead).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

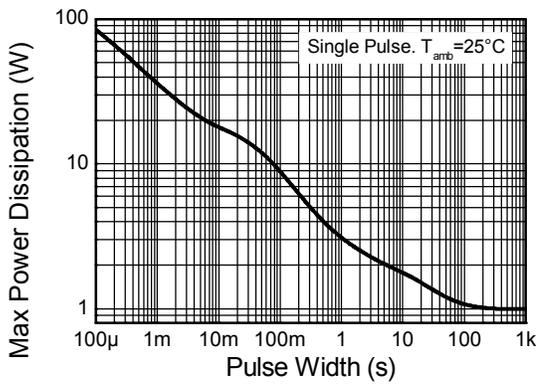
**Thermal Characteristics and Derating Information**



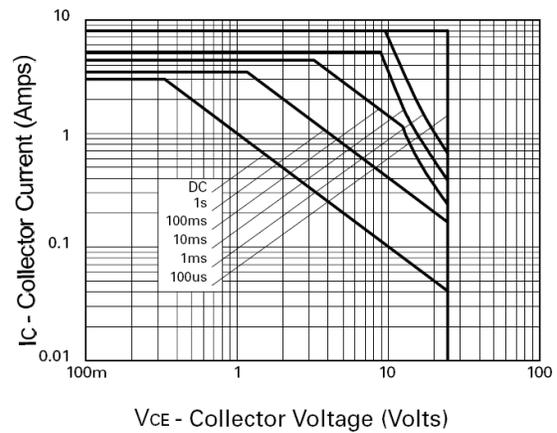
**Derating Curve**



**Transient Thermal Impedance**



**Pulse Power Dissipation**



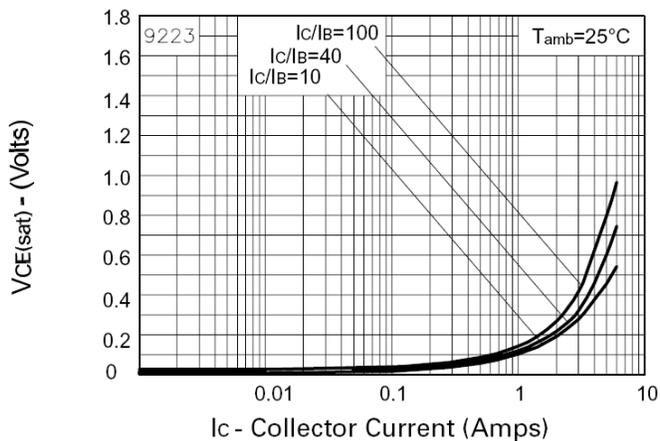
**Safe Operating Area**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

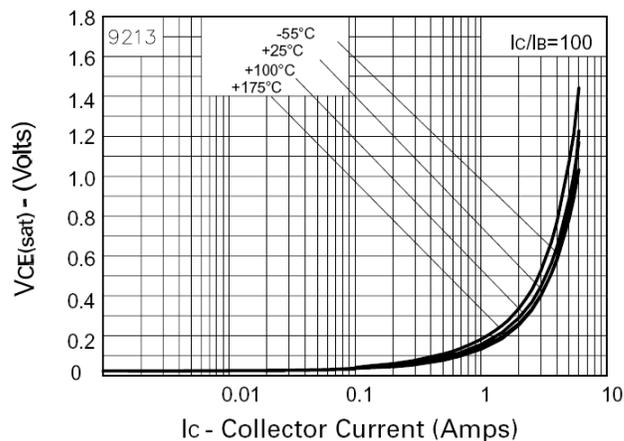
Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-25	-	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-25	-	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.1	-	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CBO</sub>	-	<1	-100	nA	V <sub>CB</sub> = -15V
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-100	nA	V <sub>EB</sub> = -5.6V
DC current transfer Static ratio (Note 9)	h <sub>FE</sub>	300	500	800	-	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V
		230	320	-		I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
		180	250	-		I <sub>C</sub> = -2A, V <sub>CE</sub> = -2V
		75	120	-		I <sub>C</sub> = -6A, V <sub>CE</sub> = -2V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	-	-130	-190	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA
		-	-290	-400		I <sub>C</sub> = -2A, I <sub>B</sub> = -20mA
		-	-250	-320		I <sub>C</sub> = -3A, I <sub>B</sub> = -100mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	-0.8	-0.9	V	I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA
Base-Emitter Turn-on Voltage (Note 9)	V <sub>BE(on)</sub>	-	-0.8	-	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
Transitional Frequency	f <sub>T</sub>	100	-	-	MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5V f = 50MHz
Input capacitance	C <sub>ibo</sub>	-	225	-	pF	V <sub>EB</sub> = -0.5V, f = 1MHz,
Output capacitance	C <sub>obo</sub>	-	25	-	pF	V <sub>CB</sub> = -10V, f = 1MHz,
Switching times	t <sub>on</sub>	-	35	-	nS	I <sub>C</sub> = -500mA, V <sub>CC</sub> = -10V I <sub>B1</sub> = -I <sub>B2</sub> = -50mA
	t <sub>off</sub>		400			

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

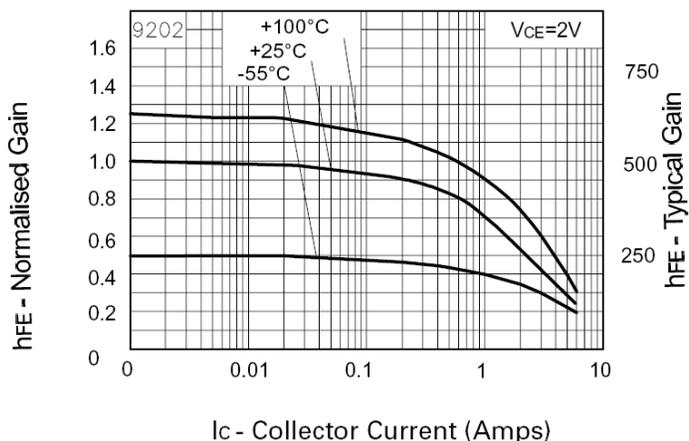
**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)



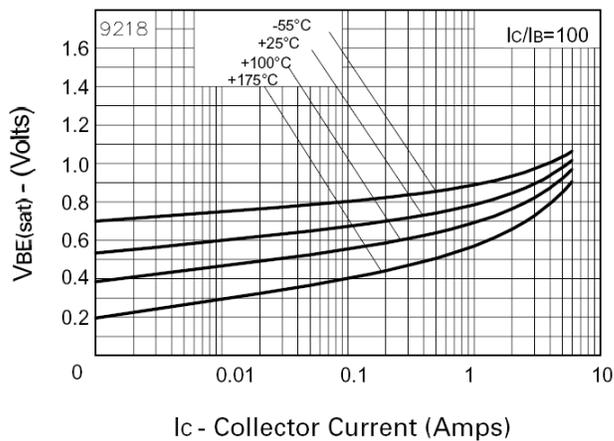
VCE(sat) v IC



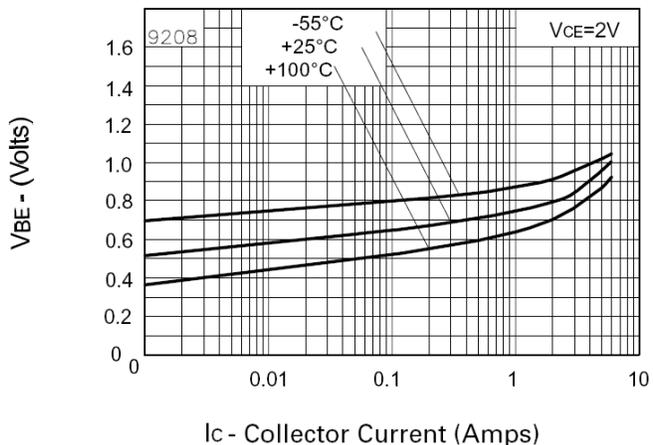
VCE(sat) v IC



hFE v IC

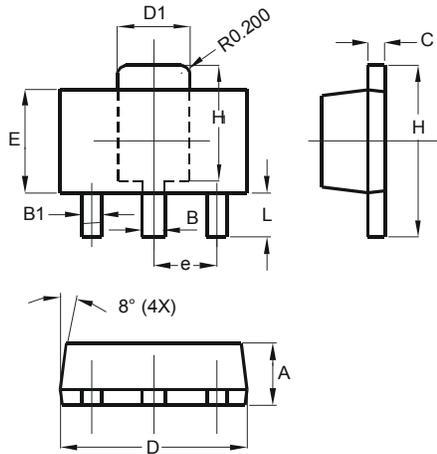


VBE(sat) v IC



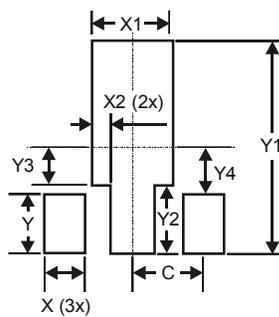
VBE(on) v IC

### Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

### Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500